



Attorney Docket 040301-0578

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

RECEIVED

MAR -8 2002

TC 2800 MAIL ROOM

Applicant: Nobutoshi AOKI et al.

Title: SEMICONDUCTOR INTEGRATED CIRCUIT INCLUDING
INSULATED GATE FIELD EFFECT TRANSISTOR AND METHOD
OF MANUFACTURING THE SAME

Appl. No.: 09/440,928

Filing Date: November 16, 1999

Examiner: S. Rao

Art Unit: 2814

7/Supp B
step 1
3-1902

**SUPPLEMENTAL
AMENDMENT AND REPLY UNDER 37 C.F.R. § 1.111**

Commissioner for Patents
Washington, D.C. 20231
Box NON-FEE

Sir:

In further reply to the Office Action mailed November 26, 2001, and supplemental to the Amendment filed February 26, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims by replacing the indicated claims with the following clean versions. (See Attachment A for the marked up version of the amended claims.)

1. (Twice Amended) A semiconductor device comprising:
a pair of main electrodes used as source and drain electrodes;
an insulating gate film adjacent to the pair of main electrodes; and
a gate electrode comprising of a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the first region.

See C17
B2